Spectroscopic, Electronic, and Mechanistic Studies of Silicon Surfaces Chemically Modified with Short Alkyl Chains

Thesis by
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As I am finishing writing this thesis and reflecting on the past ~5 years in graduate school, I am really overwhelmed with the quality of people with whom I have worked. First, I have to acknowledge my advisor Nate Lewis for working with me on some really interesting surface chemistry and giving me the chance to guide my own projects throughout graduate school. Over the years, I have developed a profound appreciation for Nate and the way he runs his research group. We are all lucky to be able to make our own mistakes, forge our own path, and build our own futures under the guidance of one of the world’s most well-known and respected chemists. Thank you, Nate, for everything you have done for me!

I have been lucky enough to have one of the most experienced and supportive committees possible in graduate school. Bill Goddard has been supportive and provided valuable advice during committee meetings and exams. Thank you, Bill, for working with me though this process! Harry Gray served as the chair of my committee, and has been incredibly encouraging throughout graduate school. Through the National Science Foundation Center for Chemical Innovation: Solar Fuels program, I have had the fantastic opportunity of working with Harry on outreach programs like Juice from Juice. Thanks to Harry, I was also supported through the CCI for my last year and some months of graduate school. Thank you Harry for supporting me and giving me a place to work on community outreach!

Bruce Brunschwig has been my fourth committee member since my props exam, but he has been my friend and surrogate advisor since I joined the Lewis group. I have
worked with Bruce since I started as a GLA in the MMRC shortly after we purchased the Dimension Icon AFM. After about 6 months with the AFM, I was moved to the much more labor-intensive XPS instruments. While I have been slowly retiring my XPS responsibilities over the last year, this job had a substantial impact, mostly good and some bad, on my experience in graduate school. Bruce always remained an invaluable resource when doing these jobs, and I really valued his support through the times when the instruments were misbehaving. Additionally, Bruce has been incredibly patient with me, particularly when it comes to charge transfer kinetics at interfaces, and I have learned so much from working with him over the years. Thank you, Bruce, for making my experience in the Lewis group better a great one!

As an XPS GLA, I got to work with some of the best Lewis group members. Taking over responsibilities from Joseph Beardslee and Judy Lattimer was quite an initial shock. Thank you to Joseph and Judy for making the transition as painless as possible! I started my GLA responsibilities with Adam Nilander and Amanda Shing, both of who remain my good friends. Thanks, Adam and Amanda! You made it fun to be a GLA and have all the power!!! Now, I’m handing responsibilities to the seasoned Jonathan Thompson, the somewhat less experienced Annelise Thompson, and the brand new Ellen Yan. All of you have helped make being a GLA, even as I drift farther away from the day-to-day responsibilities, a very positive experience. Best of luck to Jonathan, Annelise, and Ellen!

As a first year getting started in the Lewis group, I remember being overwhelmed with the range of different work that the Lewis group was doing. Coming from a
background in Vitamin B$_{12}$ kinetics, which I studied as an undergraduate, I had to find an area that interested me in a very diverse and large research group. Initially, I worked with Shane Ardo, who has been an inspiration to me since. A few months into working with Shane, Leslie O’Leary, then a graduating 5$^{th}$ year, approached me about taking on some collaborative projects involving Si surface chemistry. I had initially anticipated working with both Leslie and Shane, but the time-sensitive nature of the collaborations took priority and I soon discovered that Si surface chemistry is a full-time project. As Leslie departed for Dow Chemical a couple months after teaching me the ropes, Ron Grimm became an informal mentor in the lab. Anyone who knows Ron knows that he is truly unique and extremely multi-talented. From how to make a temperature-controlled hot plate to how to review manuscripts, Ron taught me so many of the little skills that I am so grateful to have now. Thank you Ron, Shane, and Leslie for guiding my initial few years in graduate school and providing me with the foundation to succeed!

The Lewis group, by my estimation, is by far one of the most cohesive and fun groups at Caltech, despite being spread out over 3 campus buildings. I have made such an enormous group of phenomenal friends over the years! As academia is structured around the constant revolving door of people, particularly postdocs who come and go faster than the graduate students, one has the advantage of constantly meeting new people. The disadvantage, of course, is the slow but constant stream of friends leaving for greener pastures. When I joined the Lewis group, there were 8 of us, which soon reduced to 7 and the 6. Our giant year was only rivaled and surpassed by the year that came 2 after ours. Azhar Carim, Michael Lichterman, Fadl Saadi, Nick Batara, and Victoria Dix are now all my good friends – I couldn’t have done it without you!
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I had the good fortune in graduate school of working with two amazing undergraduate students. Allison Lim came from Harvey Mudd College to work with me in Summer of 2014. She came from working with Ron Grimm while he was a temporary faculty member there, and she was very eager to learn all about semiconductor interfaces. Thank you, Allison, for making my experience as a first-time mentor a positive one. Anshul Ramachandran was my second attempt at mentoring an undergraduate, and his project picked up where Allison’s left off. I was lucky to work with both Allison and Anshul, and I am so pleased that we got to write a paper together! Good luck with graduate school, Allison, and good luck with your last couple years at Caltech, Anshul. Also, Anshul, keep up the break dancing!

I also had the great pleasure of working with Mita Dasog on the work presented in Chapter 5 of this thesis. Thank you, Mita, for working with me on this project. Without your influence, I wouldn’t have made it through that project. I also want to thank Paul Kempler, who spent some time doing a little bit of surface chemistry and looking for ferrocene in Big Bird. I know you’ll put the surface chemistry skills to good use with your
microwire project! Miguel Caban-Acevedo is carrying the silicon surface chemistry torch in the Lewis group, with Ellen, Annelise, and Josh Wiensch developing new ways to do chemistry on tricky 2-dimensional materials. Another indispensible person who must be thanked is Barbara Miralles. Barbara, I am so glad to have your support on the administrative end of things! Your understanding and patience have benefited us all in the Lewis group, and you really do make the world go around as far as I’m concerned.

I also want to devote a quick sentence or two to thank Azhar, Kyra Lee, and Dan Torelli + Susie Haubner for consistently serving as fantastic hosts for house parties. I had so much fun hanging out at your respective places! We will definitely be having a few more parties before I am out of here for good! The atmosphere that you created in the Lewis group has helped dull a lot of the stress and tension that is built into Caltech, and your influence on the group has been invaluable. I honestly have a hard time coming to the realization that our parties left together are limited.

Lastly, I want to thank my family, who has always encouraged me to do my best and find the career I love. Dad always provided me with level headed advice and has not steered me wrong yet! Mom always was a great listener whenever I had something that was bothering me or when I just needed to talk about something. I truly adore my parents, and I hope I can be like them someday. My sister, Rachel, is absolutely without a doubt my favorite person in the world. Somehow, she and I have developed a nearly identical sense of humor, and all of our conversations leave me in such a good mood. Thank you, mom, dad, and Rachel, for all of your support over the years and also keeping up with me all the way from Ohio! I love you all!
ABSTRACT

The chemical, structural, and electronic properties of semiconductor surfaces are known to strongly influence the energetics at semiconductor interfaces. Inexpensive and scalable wet chemical modification of semiconductor surfaces provides a means to impart a desired functionality at semiconductor interfaces for the development of new devices based on precise and cost-effective chemistry. This thesis is composed of three studies that focused on identifying the spectroscopic, electronic, and mechanistic properties of reactions at Si surfaces. First, ethynyl- and propynyl-terminated Si(111) surfaces were prepared and characterized by vibrational and photoelectron spectroscopy as well as electrochemical scanning-tunneling microscopy. Ethynyl-terminated Si(111) exhibited $\equiv$C–H, C≡C, Si–C stretching signals and a fractional monolayer (ML) coverage ($\Phi$) of $\Phi_{\text{Si}^{-}\text{CCH}} = 0.63 \pm 0.08$ ML and $\Phi_{\text{Si}^{-}\text{OH}} = 0.35 \pm 0.03$ ML. Propynyl-terminated Si(111) showed (C–H)$_{\text{CH}_3}$ bending, Si–C stretching, and C≡C stretching with $\Phi_{\text{Si}^{-}\text{CCCH}_3} = 1.05 \pm 0.06$ ML. Deprotonation of ethynyl-terminated Si(111) surfaces formed a unique surface-bound lithium acetylide that acted as nucleophile. This work provides definitive spectroscopic and microscopic evidence for the covalent attachment of ethynyl and propynyl groups to the Si(111) surface.

Second, Si(111) surfaces were modified with 3,4,5-trifluorophenylacetylene (TFPA) groups to impart a positive dipole at the Si(111) surface. This negative surface dipole provides the necessary band-edge shift at the Si surface to maximize the interface between p-type Si and the proton reduction half reaction. Vibrational and photoelectron spectroscopy provided evidence for the attachment of TFPA groups to the Si(111) surface. Mixed methyl/TFPA monolayers were prepared and characterized using electrochemical...
and photoelectrochemical methods to show that the band-edge positions and open-circuit voltages were shifted positive with increasing fractional TFPA coverage on the surface. This work demonstrates that monolayer chemistry can be used to manipulate the band-edge positions of Si surfaces as a function of surface composition.

Finally, mechanistic studies of the reaction of liquid methanol with hydride-terminated Si(111) surfaces in the presence of an oxidant were carried out. Vibrational and photoelectron spectroscopy showed that acetylferrrocenium, ferrocenium, and dimethylferrocenium could serve as oxidants to promote an increased rate of methoxylation of the H–Si(111) surface in the dark. Illumination of intrinsic and n-type surfaces resulted in an increased rate of methoxylation, resulting from a positive shift in energy of the electron quasi-Fermi level in the presence of light. The results are described in the context of a kinetic charge transfer formalism that is consistent with the experimentally observed results. This work provides a general framework to describe the kinetics of charge transfer reactions that occur on semiconductor surfaces.
PUBLISHED CONTENT AND CONTRIBUTIONS


Plymale, N. T. participated in the conception of the project, performed the sample preparation, collected the majority of the data, performed the data analysis, and participated in writing the manuscript.

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Plymale, N. T. participated in the conception of the project, the sample preparation, the data collection, the data analysis, and the writing of the manuscript.
# TABLE OF CONTENTS

<table>
<thead>
<tr>
<th>Section</th>
<th>Page</th>
</tr>
</thead>
<tbody>
<tr>
<td>Acknowledgements</td>
<td>iii</td>
</tr>
<tr>
<td>Abstract</td>
<td>viii</td>
</tr>
<tr>
<td>Published Content and Contributions</td>
<td>x</td>
</tr>
<tr>
<td>Table of Contents</td>
<td>xi</td>
</tr>
<tr>
<td>List of Figures</td>
<td>xv</td>
</tr>
<tr>
<td>List of Schemes</td>
<td>xx</td>
</tr>
<tr>
<td>List of Tables</td>
<td>xxi</td>
</tr>
<tr>
<td><strong>Chapter 1: Alkyl-Terminated Silicon Surfaces</strong></td>
<td>1</td>
</tr>
<tr>
<td>1.1 Hydrogen-Terminated Silicon Surfaces</td>
<td>1</td>
</tr>
<tr>
<td>1.2 Halogen-Terminated Silicon Surfaces</td>
<td>5</td>
</tr>
<tr>
<td>1.3 Methyl-Terminated Silicon Surfaces</td>
<td>6</td>
</tr>
<tr>
<td>1.4 Surface Chemistry Applications</td>
<td>15</td>
</tr>
<tr>
<td>1.5 References</td>
<td>22</td>
</tr>
<tr>
<td>**Chapter 2: Synthesis, Characterization, and Reactivity of Ethynyl-</td>
<td>33</td>
</tr>
<tr>
<td>Terminated Si(111) Surfaces</td>
<td>33</td>
</tr>
<tr>
<td>2.1 Introduction</td>
<td>36</td>
</tr>
<tr>
<td>2.2 Experimental Section</td>
<td>36</td>
</tr>
<tr>
<td>2.2.1 Materials and Methods</td>
<td>36</td>
</tr>
<tr>
<td>2.2.2 Instrumentation</td>
<td>41</td>
</tr>
<tr>
<td>2.2.3 Data Analysis</td>
<td>44</td>
</tr>
<tr>
<td>2.3 Results</td>
<td>49</td>
</tr>
<tr>
<td>2.3.1 Transmission Infrared Spectroscopy</td>
<td>49</td>
</tr>
<tr>
<td>2.3.2 High-Resolution Electron Energy-Loss Spectroscopy</td>
<td>52</td>
</tr>
<tr>
<td>2.3.3 X-ray Photoelectron Spectroscopy</td>
<td>55</td>
</tr>
<tr>
<td>2.3.4 Atomic-Force Microscopy, Electrochemical Scanning-Tunneling</td>
<td>60</td>
</tr>
<tr>
<td>Microscopy, and Low Energy Diffraction</td>
<td>64</td>
</tr>
<tr>
<td>2.3.5 Surface Recombination Velocity Measurements</td>
<td>63</td>
</tr>
<tr>
<td>2.3.6 Reactivity of HCC–Si(111) Surfaces</td>
<td>64</td>
</tr>
</tbody>
</table>
2.4 Discussion ........................................................................................................... 71
2.4.1 Vibrational Spectroscopy of HCC–Si(111) Surfaces.............................. 71
2.4.2 Surface Ordering, Stability, and Defects of HCC–Si(111) Surfaces ................................................................. 73
2.4.3 Reactivity of HCC–Si(111) Surfaces ......................................................... 75
2.4.4 Comparison with Previously Reported Syntheses and Surface Spectroscopy ....................................................... 76
2.5 Conclusions ....................................................................................................... 79
2.6 References ........................................................................................................ 80

Chapter 3: Synthesis and Characterization of Propynyl-Terminated Si(111) Surfaces ................................................................. 90
3.1 Introduction ....................................................................................................... 90
3.2 Experimental Section ....................................................................................... 92
3.2.1 Materials and Methods ............................................................................. 92
3.2.2 Instrumentation ......................................................................................... 94
3.2.3 Data Analysis .............................................................................................. 94
3.3 Results ............................................................................................................... 96
3.3.1 Transmission Infrared Spectroscopy ....................................................... 96
3.3.2 High-Resolution Electron Energy-Loss Spectroscopy ......................... 98
3.3.3 X-ray Photoelectron Spectroscopy .......................................................... 101
3.3.4 Atomic-Force Microscopy, Electrochemical Scanning-Tunneling Microscopy, and Low-Energy Electron Diffraction ................................................................................. 105
3.3.5 Surface Recombination Velocity Measurements .................................. 108
3.4 Discussion ....................................................................................................... 110
3.4.1 Vibrational Spectroscopy of CH\textsubscript{3}CC–Si(111) Surfaces ...... 110
3.4.2 Surface Ordering, Stability, and Defects of CH\textsubscript{3}CC–Si(111) Surfaces ......................................................................................................................... 111
3.4.3 Comparison with Previously Reported Syntheses and Surface Spectroscopy ................................................................................. 114
### 3.5 Conclusions

The conclusions section of this chapter highlights the key findings and implications of the research on controlling the band-edge positions of crystalline Si(111) by surface functionalization with 3,4,5-trifluorophenylacetylene moieties. The conclusions are based on the detailed analysis presented in the results and discussion sections.

### 3.6 References

A comprehensive list of references is provided at the end of the document, covering the literature that was cited throughout the chapter.

---

**Chapter 4: Control of the Band-Edge Positions of Crystalline Si(111) by Surface Functionalization with 3,4,5-Trifluorophenylacetylene Moieties**

4.1 Introduction

4.2 Experimental Section

4.2.1 Materials and Methods

4.2.2 Instrumentation

4.2.3 Data Analysis

4.3 Results

4.3.1 Spectroscopic Characterization and Surface Recombination Velocity of Si(111)--TFPA and Si(111)--MMTFPA Surfaces

4.3.2 Hg Contacts to Si(111)--MMTFPA Surfaces

4.3.3 Photoelectrochemical Behavior of Si(111)--TFPA and Si(111)--MMTFPA Surfaces in Contact with CH3CN--Cp*2Fe+/0

4.3.4 Photoelectrochemical Behavior of Si(111)--TFPA and Si(111)--MMTFPA Surfaces in Contact with CH3CN--MV2+/+•

4.4 Discussion

4.4.1 Si(111)--TFPA Surface Characterization

4.4.2 Hg Contacts to Si(111)--MMTFPA Surfaces

4.4.3 Photoelectrochemical Measurements of Si(111)--TFPA and Si(111)--MMTFPA Surfaces in CH3CN

4.5 Conclusions

4.6 References

---

**Chapter 5: A Mechanistic Study of the Oxidative Reaction of Hydrogen-Terminated Si(111) Surfaces with Liquid Methanol**

5.1 Introduction

5.2 Experimental Section

5.2.1 Materials and Methods

5.2.2 Instrumentation

5.2.3 Data Analysis

5.3 Results

5.3.1 Spectroscopic Characterization of Si(111)--TFPA and Si(111)--MMTFPA Surfaces

5.3.2 Hg Contacts to Si(111)--MMTFPA Surfaces

5.3.3 Photoelectrochemical Behavior of Si(111)--TFPA and Si(111)--MMTFPA Surfaces in Contact with CH3CN--Cp*2Fe+/0

5.4 Discussion

5.4.1 Si(111)--TFPA Surface Characterization

5.4.2 Hg Contacts to Si(111)--MMTFPA Surfaces

5.4.3 Photoelectrochemical Measurements of Si(111)--TFPA and Si(111)--MMTFPA Surfaces in CH3CN

5.5 Conclusions

5.6 References
5.1 Introduction .................................................................................................................. 179
5.2 Experimental Section .................................................................................................. 182
  5.2.1 Materials and Methods ......................................................................................... 182
  5.2.2 Instrumentation ..................................................................................................... 187
  5.2.3 Analysis of TIRS and XPS Data .......................................................................... 188
5.3 Results ......................................................................................................................... 190
  5.3.1 Reaction of H–Si(111) with CH₃OH Solutions in the Dark ......................... 190
  5.3.2 Reaction of H–Si(111) with CH₃OH Solutions in the Presence of Light .......... 200
  5.3.3 Analysis of F Content on H–Si(111) Surfaces Reacted in CH₃OH Solutions .... 202
  5.3.4 Potentiostatic reaction of H–Si(111) with CH₃OH ............................................ 202
5.4 Discussion ................................................................................................................... 207
  5.4.1 Kinetic Description and Mechanism of Oxidant-Activated Methoxylolation of H–Si(111) Surfaces ................................................................. 207
  5.4.2 Kinetic Description and Mechanism of the Potentiostatic Methoxylolation of H–Si(111) Surfaces ................................................................. 216
5.5 Conclusions ................................................................................................................ 220
5.6 References .................................................................................................................. 222
## LIST OF FIGURES

<table>
<thead>
<tr>
<th>Number</th>
<th>Description</th>
<th>Page</th>
</tr>
</thead>
<tbody>
<tr>
<td>1.1</td>
<td>TIRS data for the H–Si(111) surface</td>
<td>3</td>
</tr>
<tr>
<td>1.2</td>
<td>TIRS data for CH₃–Si(111) surfaces</td>
<td>7</td>
</tr>
<tr>
<td>1.3</td>
<td>HREELS data for CH₃–Si(111) surfaces</td>
<td>8</td>
</tr>
<tr>
<td>1.4</td>
<td>High-resolution XP spectra of the C 1s and Si 2p regions for CH₃–Si(111) surfaces</td>
<td>11</td>
</tr>
<tr>
<td>1.5</td>
<td>Representative topographical AFM image of the CH₃–Si(111) Surface</td>
<td>12</td>
</tr>
<tr>
<td>1.6</td>
<td>Representative LEED pattern for a CH₃–Si(111) surface</td>
<td>13</td>
</tr>
<tr>
<td>1.7</td>
<td>S behavior as a function of time exposed to air for CH₃–Si(111) Surfaces</td>
<td>14</td>
</tr>
<tr>
<td>1.8</td>
<td>Example of linker chemistry that could be used to integrate catalyst nanoparticles with semiconductors</td>
<td>16</td>
</tr>
<tr>
<td>1.9</td>
<td>Example of linker chemistry that could be used to control metal deposition on a Si surface</td>
<td>17</td>
</tr>
<tr>
<td>1.10</td>
<td>Example of a silicon/polymer junction formed by a covalent bond between the two materials</td>
<td>19</td>
</tr>
<tr>
<td>1.11</td>
<td>Example of a silicon/metal oxide junction formed by atomic layer deposition</td>
<td>21</td>
</tr>
<tr>
<td>2.1</td>
<td>TIRS data for HCC–Si(111) surfaces prepared using DMSO</td>
<td>50</td>
</tr>
<tr>
<td>2.2</td>
<td>TIRS data for HCC–Si(111) surfaces prepared using DMA</td>
<td>51</td>
</tr>
<tr>
<td>2.3</td>
<td>TIRS data for CH₃–Si(111) and HCC–Si(111) surfaces referenced to the SiOₓ surface</td>
<td>52</td>
</tr>
<tr>
<td>2.4</td>
<td>HREELS data for HCC–Si(111) surfaces</td>
<td>53</td>
</tr>
<tr>
<td>2.5</td>
<td>High-resolution XP spectrum of the C 1s region for HCC–Si(111) surfaces</td>
<td>55</td>
</tr>
</tbody>
</table>
2.6 High-resolution XP spectrum of the Si 2p region for HCC–Si(111) Surfaces ................................................................. 56
2.7 Thermal stability in vacuum of HCC–Si(111) surfaces ............ 58
2.8 Topographical AFM image of the HCC–Si(111) surface .......... 60
2.9 EC-STM image of the HCC–Si(111) surface ......................... 61
2.10 Representative LEED pattern for the HCC–Si(111) surface ...... 62
2.11 S measured as a function of air exposure for CH3–Si(111) and HCC–Si(111) surfaces .................................................. 63
2.12 TIRS data for HCC–Si(111) surfaces collected at 74° incidence after treatment with t-BuLi followed by CD3OD .......... 65
2.13 TIRS data for HCC–Si(111) surfaces collected at 30° incidence after treatment with t-BuLi followed by CD3OD ............ 65
2.14 TIRS data collected at 74° incidence angle for HCC–Si(111) surfaces after treatment with strong bases followed by reaction with CD3OD. ......................................................... 66
2.15 TIRS data collected 74° incidence angle referenced to the SiOx surface before and after treatment with t-BuLi followed by CD3OD .................................................................. 67
2.16 High-resolution F 1s XP spectra of CH3–Si(111) HCC–Si(111), CH3CC–Si(111), and SiOx surfaces after reaction with t-BuLi followed by 4-fluorobenzyl chloride ............................................. 70
3.1 TIRS data for CH3CC–Si(111) surfaces .................................. 97
3.2 TIRS data for the CH3CC–Si(111) surface referenced to the SiOx surface ........................................................................ 98
3.3 HREELS data for CH3CC–Si(111) surfaces ............................ 99
3.4 High-resolution XP spectrum of the C 1s region for CH3CC– Si(111) surfaces ................................................................... 101
3.5 High-resolution XP spectrum of the Si 2p region for CH3CC–Si(111) surfaces ................................................................. 102
3.6 Thermal stability in vacuum of CH3CC–Si(111) surfaces ......... 104
3.7 Topographical AFM image of a CH$_3$CC–Si(111) surface...........106
3.8 Representative EC-STM image a CH$_3$CC–Si(111) surface...........107
3.9 Representative LEED pattern for a CH$_3$CC–Si(111) surface .......108
3.10 S measured as a function of exposure to air for CH$_3$–Si(111) and CH$_3$CC–Si(111) surfaces.........................................................109
4.1 Effect of a surface dipole on the band-edge positions and barrier height, $\Phi_b$, for a p-type semiconductor..............................127
4.2 The Teflon reaction vessels used to isolate the Al-coated side of p-Si electrodes.................................................................133
4.3 TIRS data for a Si(111)–TFPA surface collected at 74° and 30° with respect to the surface normal.................................................145
4.4 TIRS data for a Si(111)–MMTFPA surface with $\theta_{\text{TFPA}} = 0.16$ ML collected at 74° with respect to the surface normal ..........147
4.5 S values for Si(111)–CH$_3$, Si(111)–MMTFPA, and Si(111)–TFPA surfaces as a function of $\theta_{\text{TFPA}}$........................................147
4.6 XPS data for an n-Si(111)–MMTFPA surface with $\theta_{\text{TFPA}} =$ 0.11 ML.........................................................................................149
4.7 XPS data for the Si(111)–TFPA surface with $\theta_{\text{TFPA}} = 0.35$ ML.....150
4.8 Representative two-electrode $J-V$ behavior for n-type and p-type Si(111)–MMTFPA/Hg junctions .............................................151
4.9 Correlation between the calculated barrier height for Si(111)–MMTFPA/Hg junctions and the fractional monolayer coverage of TFPA for n-type and p-type samples.............................................153
4.10 Representative $J-E$ data under 100 mW cm$^{-2}$ simulated sunlight illumination for functionalized Si(111) surfaces in contact with Cp*$_2$Fe$^{+0}$ .................................................................155
4.11 Representative $J-E$ data under 100 mW cm$^{-2}$ illumination for functionalized Si(111) surfaces in contact with MV$^{2+/-}$.............157
5.1 Time dependence of the reaction of H–Si(111) with neat CH$_3$OH and CH$_3$OH containing Cp$_2$Fe$^+$..............................................191
5.2 Energy diagram showing the relative energy positions of the Si bands and the formal potentials of the oxidants used .......................... 192
5.3 TIRS data for intrinsic H–Si(111) surfaces after treatment in neat CH₃OH or CH₃OH solutions containing oxidant ..................... 194
5.4 Correlation between $\theta_{\text{Si-OCH}_3}$ and the oxidizing conditions used in the reaction of H–Si(111) surfaces with CH₃OH in the dark .... 196
5.5 XPS data for the C 1s core level of H–Si(111) surfaces after exposure to neat CH₃OH or CH₃OH solutions containing oxidant ................................................................. 197
5.6 Correlation showing the area under the region containing the three $\nu(\text{C–H})_{\text{CH}_3}$ peaks as a function of the oxidizing conditions used in the reaction of H–Si(111) surfaces with CH₃OH in the dark ................................................................. 198
5.7 Correlation showing the area under the region containing the $\delta_\text{a}(\text{C–H})_{\text{CH}_3}$ and $\nu(\text{C–O}) + \rho(\text{CH}_3)$ peaks as a function of the oxidizing conditions used in the reaction of H–Si(111) surfaces with CH₃OH in the absence of light ................................................................. 200
5.8 Correlation between $\theta_{\text{Si-OCH}_3}$ and the oxidizing conditions used in the reaction of H–Si(111) surfaces with CH₃OH in the absence and presence of ambient light ................................................................. 201
5.9 High-resolution XPS data for the F 1s region of a H–Si(111) sample reacted with CH₃OH containing 1.0 mM Me₂Cp₂Fe⁺BF₄⁻ ................................................................. 203
5.10 Correlation between $\theta_F$ and the oxidizing conditions used in the reaction of H–Si(111) surfaces with CH₃OH in the absence and presence of ambient light ................................................................. 204
5.11 $J$-$E$ behavior of n-type and p-type H–Si(111) samples in contact with CH₃OH ................................................................. 205
5.12 Schematic representation of charge transfer across a semiconductor/liquid interface for oxidant-activated methoxylation .................................................................210

5.13 Schematic representation of charge transfer across a semiconductor/liquid interface for potentiostatic methoxylation ...217
# LIST OF SCHEMES

<table>
<thead>
<tr>
<th>Number</th>
<th>Description</th>
<th>Page</th>
</tr>
</thead>
<tbody>
<tr>
<td>2.1</td>
<td>Synthesis of CH₃–Si(111) and HCC–Si(111) Surfaces</td>
<td>38</td>
</tr>
<tr>
<td>2.2</td>
<td>Monolayer Thickness of Surface-Bound –CH₃, –CCH, and –OH Groups</td>
<td>47</td>
</tr>
<tr>
<td>2.3</td>
<td>Monolayer Thickness of 4-Fluorobenzyl-Modified Surfaces</td>
<td>48</td>
</tr>
<tr>
<td>3.1</td>
<td>Synthesis of CH₃CC–Si(111) Surfaces</td>
<td>94</td>
</tr>
<tr>
<td>3.2</td>
<td>Monolayer Thickness of Surface-Bound –CCCH₃ Groups</td>
<td>96</td>
</tr>
<tr>
<td>4.1</td>
<td>Synthesis of Si(111)–TFPA and Si(111)–MMTFPA Surfaces</td>
<td>132</td>
</tr>
<tr>
<td>4.2</td>
<td>Estimated Thickness of –CH₃ and TFPA Groups</td>
<td>139</td>
</tr>
<tr>
<td>5.1</td>
<td>Methoxylation of H-Si(111) Surfaces in the Absence of an Oxidant</td>
<td>181</td>
</tr>
<tr>
<td>5.2</td>
<td>Oxidant-Activated Methoxylation of H-Si(111)</td>
<td>181</td>
</tr>
</tbody>
</table>
# LIST OF TABLES

<table>
<thead>
<tr>
<th>Number</th>
<th>Page</th>
</tr>
</thead>
<tbody>
<tr>
<td>2.1</td>
<td>54</td>
</tr>
<tr>
<td>2.2</td>
<td>59</td>
</tr>
<tr>
<td>2.3</td>
<td>68</td>
</tr>
<tr>
<td>2.4</td>
<td>78</td>
</tr>
<tr>
<td>3.1</td>
<td>100</td>
</tr>
<tr>
<td>3.2</td>
<td>105</td>
</tr>
<tr>
<td>3.3</td>
<td>115</td>
</tr>
<tr>
<td>4.1</td>
<td>155</td>
</tr>
<tr>
<td>4.2</td>
<td>158</td>
</tr>
<tr>
<td>5.1</td>
<td>207</td>
</tr>
</tbody>
</table>

2.1 Summary of the Positions and Assigned Modes for the Vibrational Signatures Observed for the HCC–Si(111) Surface

2.2 Estimated Fractional Monolayer Coverage, \( \Phi \), of a HCC–Si(111) Surface as a Function of Annealing Temperature

2.3 Summary of the Positions and Assigned Modes for the Vibrational Signatures Observed for the DCC–Si(111) Surface

2.4 Summary of Prior Reports of Synthesis and Characterization of Ethynyl- Terminated Si Surfaces

3.1 Summary of the Positions and Assigned Modes for the Vibrational Signatures Observed for CH\(_3\)CC–Si(111) Surfaces

3.2 The Estimated Fractional ML Coverage, \( \Phi \), of a CH\(_3\)CC–Si(111) Surface as a Function of Annealing Temperature

3.3 Summary of Prior Reports of Synthesis and Characterization of Propynyl- Terminated Si Surfaces

4.1 \( E_{oc} \) and \( \Phi_b \) measurements for functionalized Si surfaces in contact with CH\(_3\)CN-Cp\(^\star\)Fe\(^{+/0}\)

4.2 \( E_{oc} \) and \( \Phi_b \) measurements for functionalized Si surfaces in contact with CH\(_3\)CN-MV\(^{2+/+}\)

5.1 Summary of the Quantification for the Potentiostatic Methoxylation of H–Si(111) Surfaces